Unit: mm

TOSHIBA Transistor Silicon NPN Triple Diffused Type

2SD2414(SM)

High Current Switching Applications Power Amplifier Applications

• Low collector saturation voltage: $V_{CE (sat)} = 0.5 \text{ V (max)}$ (at $I_{C} = 4 \text{ A}$)

Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit	
Collector-base voltage		V_{CBO}	100	V	
Collector-emitter voltage		V _{CEO}	80	V	
Emitter-base voltage		V _{EBO}	5	V	
Collector current		I _C	7	Α	
Base current		Ι _Β	1	Α	
Collector power dissipation	Ta = 25°C	PC	1.5	W	
	Tc = 25°C	FC	40		
Junction temperature		Tj	150	°C	
Storage temperature range		T _{stg}	-55 to 150	°C	

1. BASE
2. COLLECTOR (HEAT SINK)
3. EMITTER

JEDEC

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TOSHIBA

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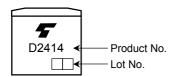
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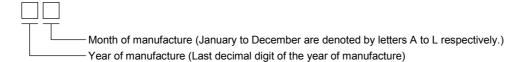
Electrical Characteristics (Ta = 25°C)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current		I _{CBO}	V _{CB} = 100 V, I _E = 0	_	_	5	μΑ
Emitter cut-off current		I _{EBO}	V _{EB} = 5 V, I _C = 0	-	_	5	μΑ
Collector-emitter	breakdown voltage	V (BR) CEO	I _C = 50 mA, I _B = 0	80	_	_	V
DC current gain		h _{FE (1)}	V _{CE} = 1 V, I _C = 1 A	100	_	320	
		h _{FE (2)}	V _{CE} = 1 V, I _C = 4 A	30	_	_	
Collector-emitter	r-emitter saturation voltage $V_{CE (sat)}$ $I_{C} = 4 \text{ A}, I_{B} = 0.4 \text{ A}$		-	0.25	0.5	V	
Base-emitter saturation voltage		V _{BE (sat)}	I _C = 4 A, I _B = 0.4 A		0.9	1.4	V
Transition frequency		f _T	V _{CE} = 4 V, I _C = 1 A		10	_	MHz
Collector output capacitance		C _{ob}	V _{CB} = 10 V, I _E = 0, f = 1 MHz	-	200	_	pF
Switching time	Turn-on time	t _{on}	20 μ s Input Inp	_	0.4	_	
	Storage time	t _{stg}		_	2.5	_	μs
	Fall time	t _f		_	0.5	_	

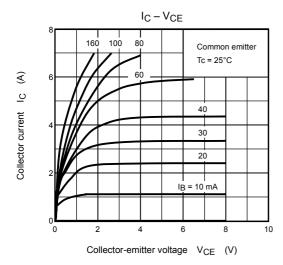
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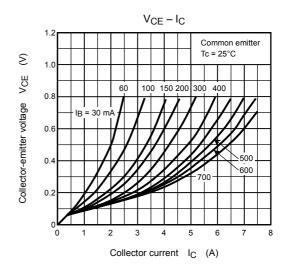


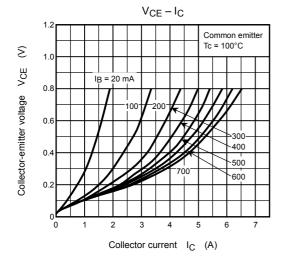
Explanation of Lot No.

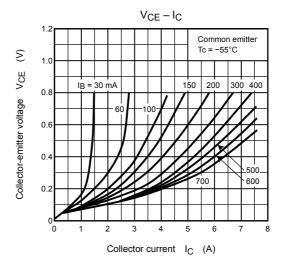


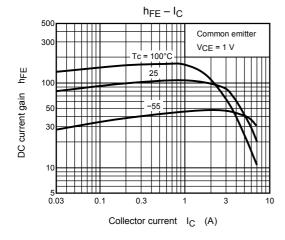
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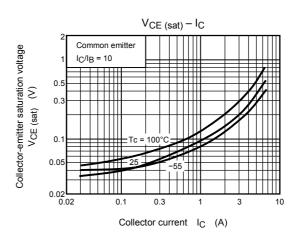


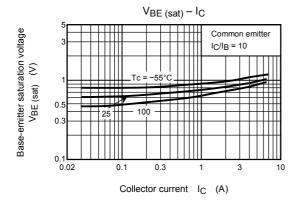


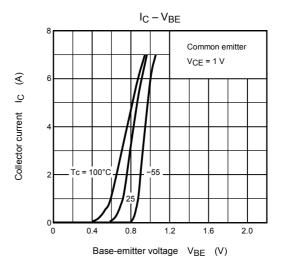


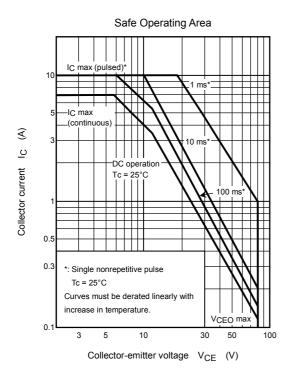












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